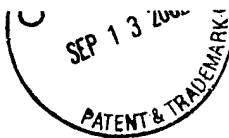


DOCKET NO.: 205927US99



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

#9/a
9/19/2
Sunder

IN RE APPLICATION OF:

: GROUP ART UNIT: 2815

NADA EL-ZEIN ET AL

SERIAL NO.: 09/624,691

: EXAMINER: JACKSON, JR, J.

FILED: JULY 24, 2000

FOR: HETEROJUNCTION TUNNELING DIODES AND PROCESS FOR
FABRICATING SAME

AMENDMENT

ASSISTANT COMMISSIONER FOR PATENTS
WASHINGTON, D.C. 20231

SIR:

Responsive to the Official Action dated June 13, 2002, please amend the above-
identified application as follows.

IN THE CLAIMS

Please cancel Claims 1-66.

Please add new claims 67-110 as follows:

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--67. A semiconductor device comprising:

a monocrystalline semiconductor substrate;

an oxide layer formed overlying the substrate;

a monocrystalline compound semiconductor layer formed overlying the oxide layer;

and